

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

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**INFORMATION DISCLOSURE
STATEMENT**

Docket Number:
2345/17A

Application Number
09/750,837

Filing Date
December 28, 2000

Examiner
Lawrence D. Ferguson

Art Unit
1774

Title
CALIBRATED SCALE IN THE NANOMETER
RANGE FOR TECHNICAL DEVICES USED FOR
THE HIGH-RESOLUTION OR ULTRAHIGH-
RESOLUTION IMAGING OF STRUCTURES

Applicant(s)
Rainer LOESCH et al.

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

1. In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and in conformance with the procedures of 37 C.F.R. §§ 1.97 and 1.98 and M.P.E.P. § 609, attorneys for Applicant(s) hereby bring the following reference(s) to the attention of the Examiner. The reference(s) are listed on the attached modified PTO Form No. 1449. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.
2. A copy of each patent, publication or other information listed on the modified PTO form 1449 is enclosed, except as otherwise indicated on the modified PTO form 1449.
3. The Commissioner is authorized to charge the fee under 37 C.F.R. § 1.17(p) of \$180.00; to Deposit Account No. **11-0600**, and is also authorized (as appropriate or necessary) to charge any additional fees or credit any overpayment to Deposit Account No. **11-0600**. A duplicate copy of this paper is enclosed for that purpose.

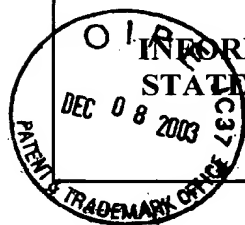
Dated: Dec-8, 2003

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
PTO FORM 1449**

ATTY. DOCKET NO.
2345/17A

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GROUP
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
				YES	NO
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EXAMINER	DATE CONSIDERED
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

